

**2SJ268**

Ultrahigh-Speed Switching Applications

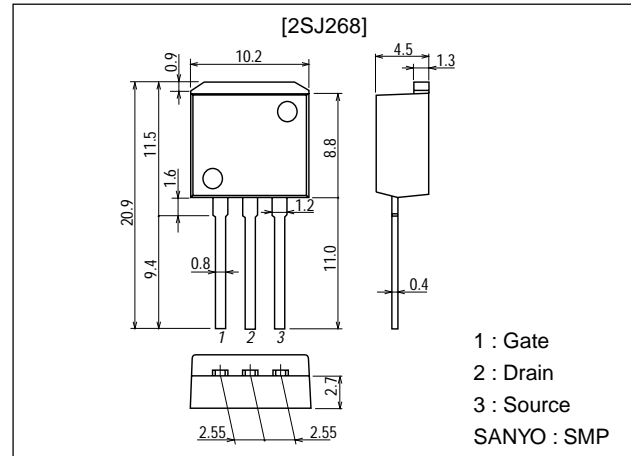
Features

- Low ON resistance.
- Ultrahigh-speed switching.
- Low-voltage drive.
- Surface mount type device making the following possible.
- Reduction in the number of manufacturing processes for 2SJ268-applied equipment.
- High density surface mount applications.
- Small size of 2SJ268-applied equipment.

Package Dimensions

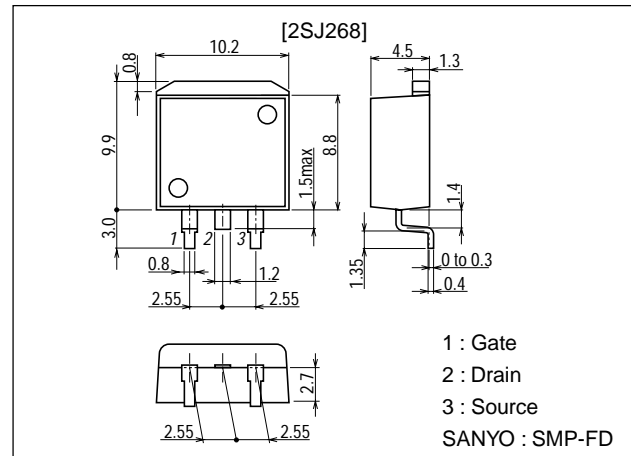
unit:mm

2093A



unit:mm

2090A



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Specifications

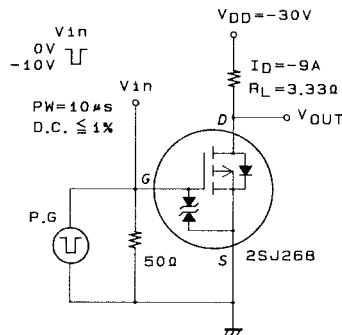
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-60	V
Gate-to-Source Voltage	V_{GSS}		± 15	V
Drain Current (DC)	I_D		-18	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-72	A
Allowable Power Dissipation	P_D		1.65	W
		$T_c = 25^\circ\text{C}$	70	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150	$^\circ\text{C}$

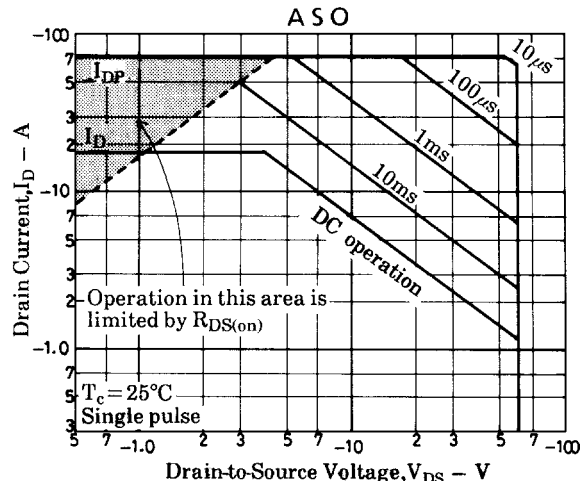
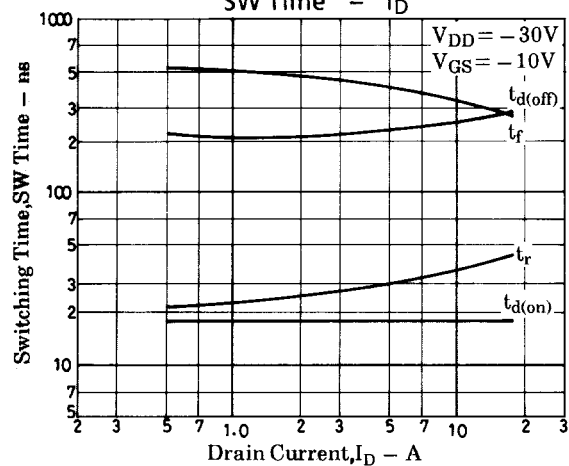
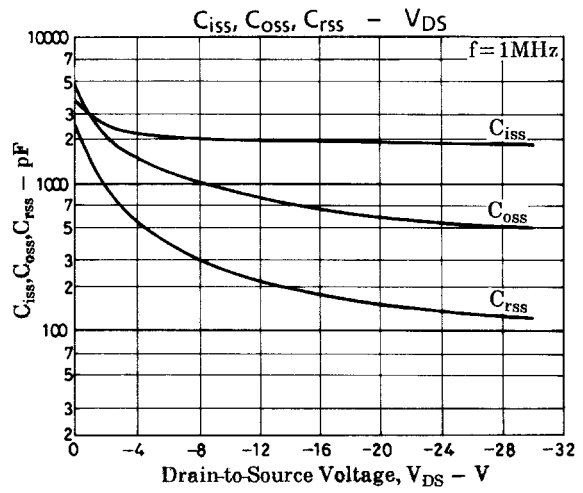
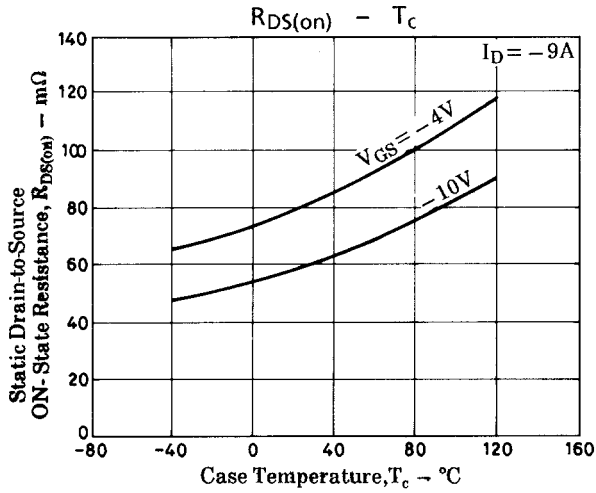
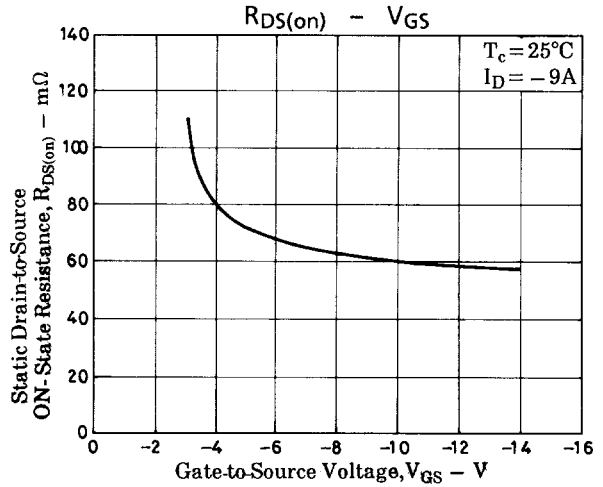
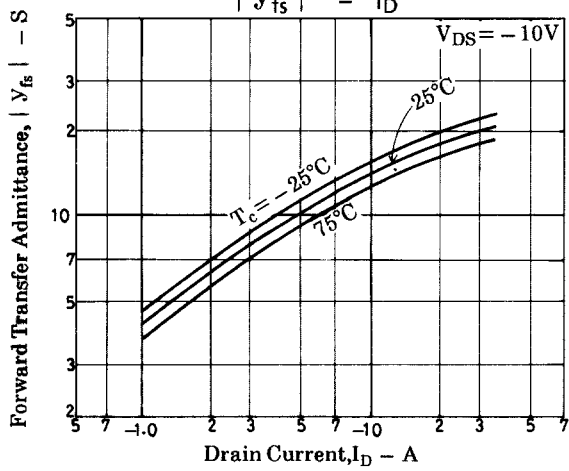
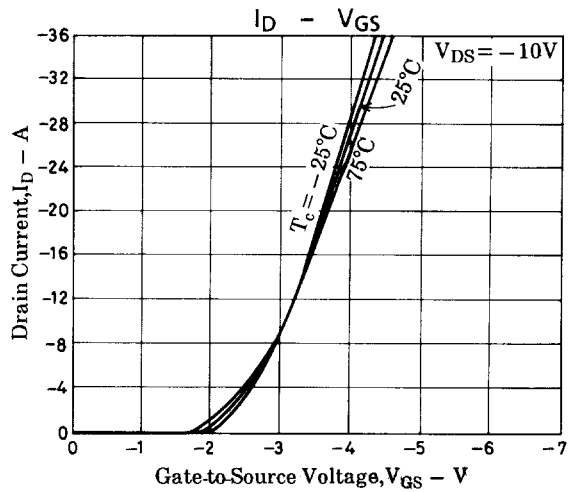
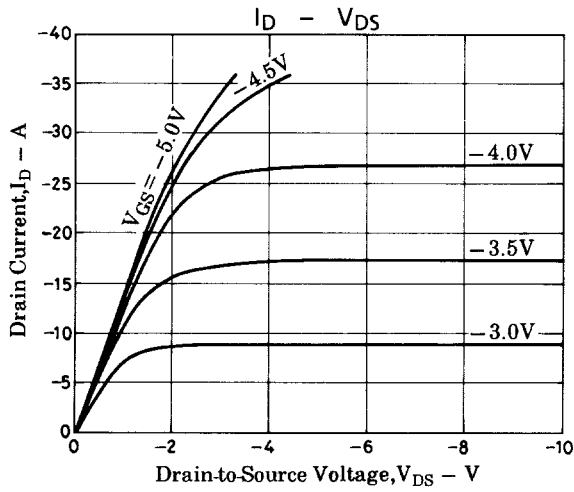
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$, $V_{GS} = 0$	-60			V
Gate-to-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu\text{A}$, $V_{DS} = 0$	± 15			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{V}$, $V_{GS} = 0$			-100	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12\text{V}$, $V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{V}$, $I_D = -9\text{A}$	8	13.5		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -9\text{A}$, $V_{GS} = -10\text{V}$		60	80	$\text{m}\Omega$
	$R_{DS(on)}$	$I_D = -9\text{A}$, $V_{GS} = -4\text{V}$		80	110	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -20\text{V}$, $f = 1\text{MHz}$		1900		pF
Output Capacitance	C_{oss}	$V_{DS} = -20\text{V}$, $f = 1\text{MHz}$		600		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20\text{V}$, $f = 1\text{MHz}$		150		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		18		ns
Rise Time	t_r	See specified Test Circuit		35		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		350		ns
Fall Time	t_f	See specified Test Circuit		250		ns
Diode Forward Voltage	V_{SD}	$I_S = -18\text{A}$, $V_{GS} = 0$		-1.0	-1.5	V

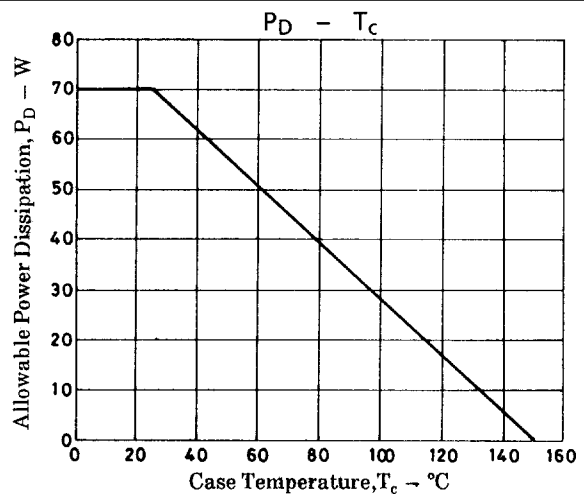
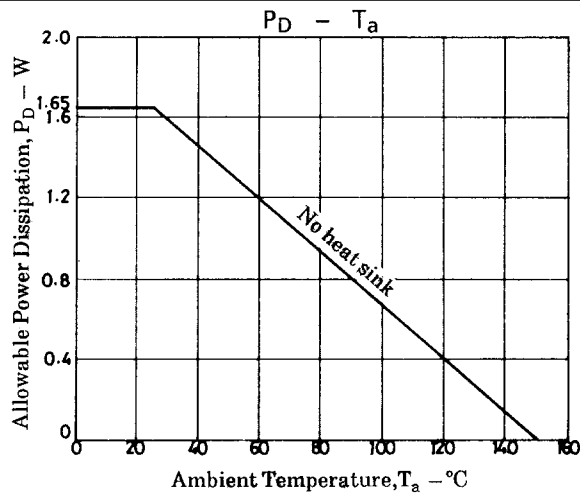
Switching Time Test Circuit



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